



AMERICAS SALES CONFERENCE

# AAMS Automotive Si MOSFET Divisional Presentation

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March 9-12, 2026



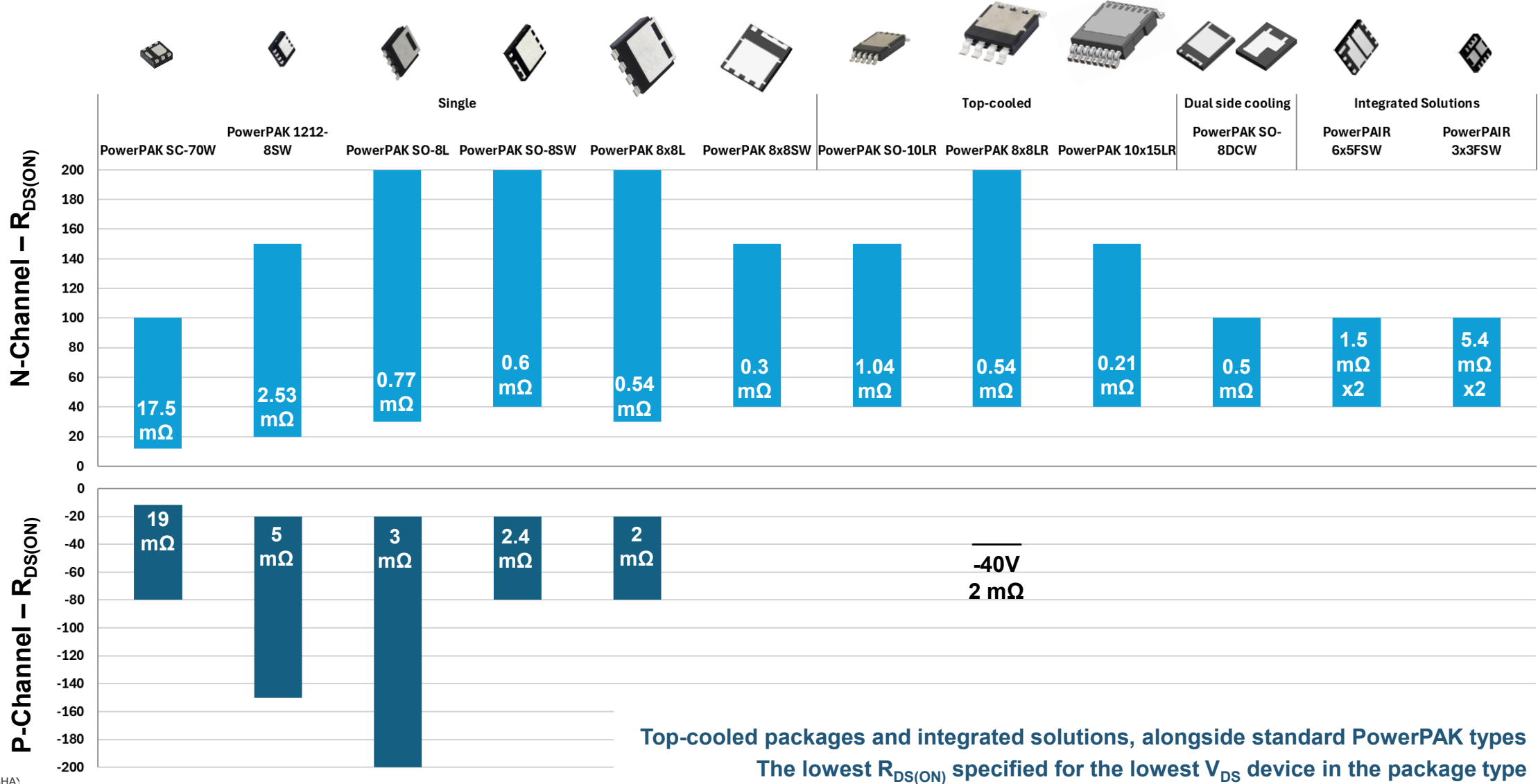
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# Broadline Si Portfolio – One-Stop Shop








## $V_{DS}$ and Package Types



# Vishay MOSFET Solutions Applications Alignment



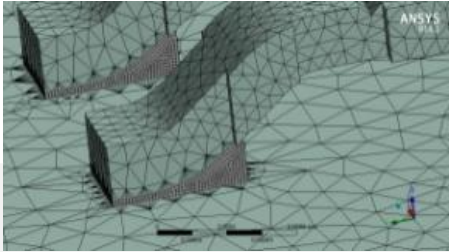
Automotive Applications	Vishay MOSFET Technology			
	MaxSiC 750 V to 1200 V	TrenchFET 40 V to 150 V	P-Channel TrenchFET	PowerPAIR
	 <p>TO-247 TO-247-4 TO-263-7</p>	 <p>8x8L 8x8LR SO-10LR SO8SW / SO8L 80V to 150V 80V to 150V 80V to 150V 80V to 150V</p>	 <p>8x8L SO8SW / SO8L 80V to 150V 80V to 150V</p>	 <p>PowerPAIR 40V to 100V</p>
800 V OBC	VISHAY			
Battery Management DC/DC (800 V)	VISHAY			
Battery Management Systems	VISHAY	VISHAY	VISHAY	
Traction Inverters	VISHAY	VISHAY		
Powertrain Electrification and E-Mobility	VISHAY	VISHAY	VISHAY	VISHAY
EPS and Steer by Wire		VISHAY	VISHAY	VISHAY
Braking Systems		VISHAY	VISHAY	
Domain and Zonal Control		VISHAY	VISHAY	VISHAY
Body Electronics, Convenience, PDU		VISHAY	VISHAY	VISHAY
ADAS and Infotainment		VISHAY	VISHAY	VISHAY

- 750 V and 1200 V MaxSiC devices for 400 V and 800 V applications
- 40 V to 150 V TrenchFET Gen IV and V products for 12 V to 96 V power nets
- Leading p-channel portfolio for 12 V and 48 V applications and reverse protection
- Top-cooled packages optimized for heatsink or cold plate cooling
- Integrated solutions available for increasing power density



# Strategic Pillars and Technology Evolution

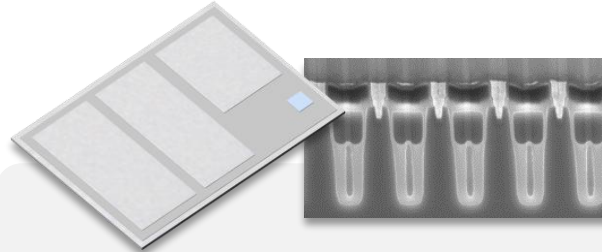
## For Efficient, Compact, and More Reliable Automotive Electronic Systems



### Designed Beyond AEC-Q101

#### High Reliability in Critical High Stress Applications

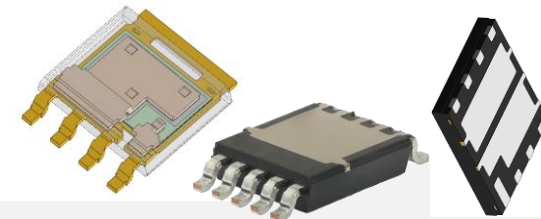
- New packages are engineered for maximum mechanical stress relief
- Comprehensive BLR testing and reporting (**vibration, bending, thermal shock, power temp cycling**)
- Continuous improvement mindset
- **~6 PPB valid annual return rate (last 5 years of data)**



### High Performance Silicon

#### N- & P-Channel MOSFETs

- With  $BV_{DSS}$  from -200 V to 650 V
- Five generations of TrenchFET® evolution
- **Gen 5 rolling out now: 40 V, 80 V, 100 V, 150 V**
- P-channel TrenchFET with industry best  $R_{DS(ON)}$
- **Gen 4 released @ -60 V, -80 V, and -100 V**
- 650V E series superjunction
- **Unique 175 °C rating**



### Broad Package Selections

#### Solutions for Increasing Power Density

- PowerPAK® packages
- **Bond-wireless form factors**
- Multi-die solutions optimized for specific applications
- **PowerPAIR – dual half-bridge**
- Top-cooled packaging
- KGD (known good die) portfolio
- **Latest technologies available**

# Segment, Customers, Applications

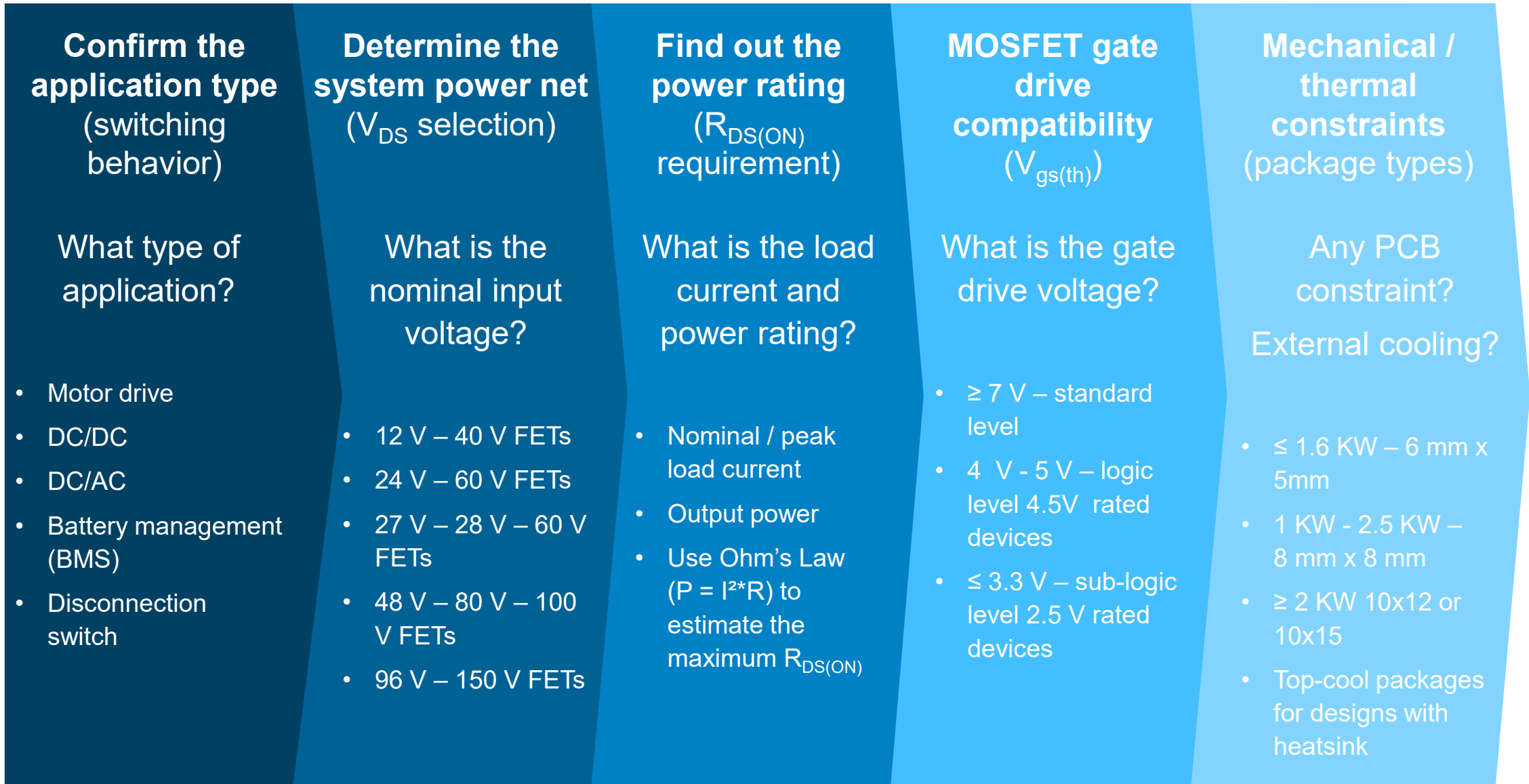
Where to Hunt and How to Win

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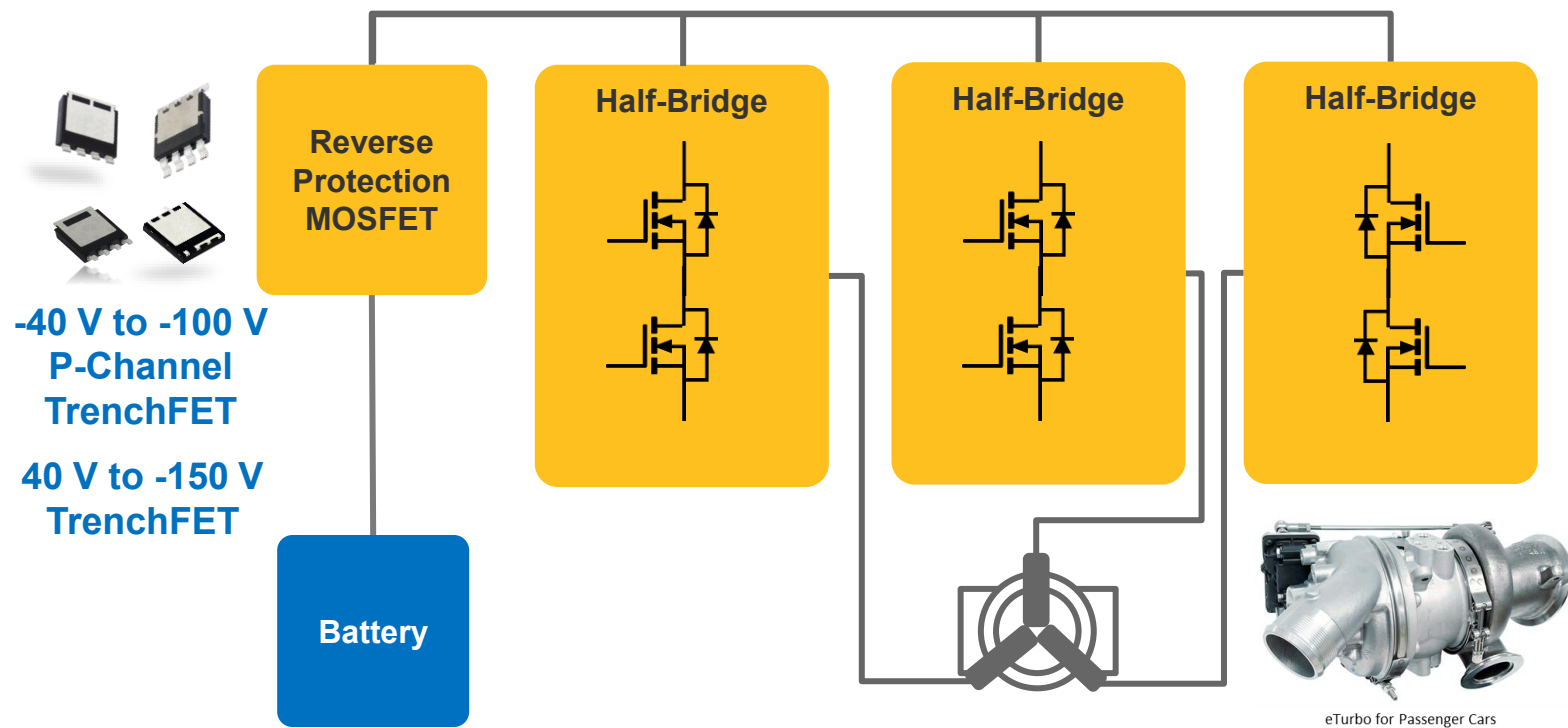
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# Customer Discovery Framework





# Electrification - Motor Drive Inverters / BLDC Motors



## 40 V to 200 V TrenchFET

-  -40 V to -100 V P-Channel TrenchFET
-  40 V to -150 V TrenchFET

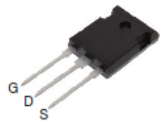
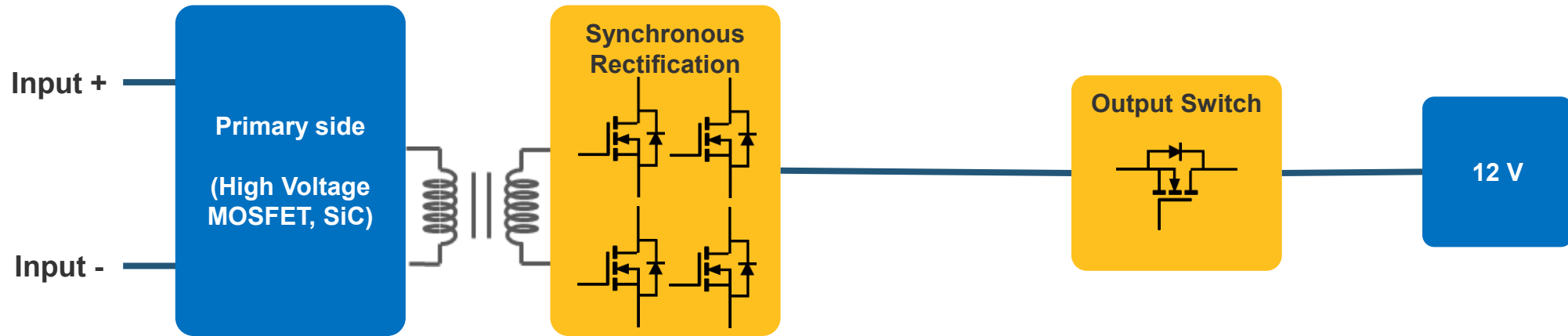
-  **PowerPAK 8x8L**  
8 x 8 mm<sup>2</sup>
-  **PowerPAK 8x8LR**  
Top-cooled 8 x 8 mm<sup>2</sup>
-  **PowerPAK SO-8SW**  
6 x 5 mm<sup>2</sup>
-  **PowerPAK SO-8L**  
6 x 5 mm<sup>2</sup> with gullwing leads
-  **PowerPAK SO-10LR**  
7 x 5 mm<sup>2</sup> top-cooled package
-  **Known Good Die (KGD)**  
Bare die in tape and reel
-  **PowerPAIR 6x5FSW**  
6 x 5 mm<sup>2</sup>  
Integrated MOSFET half-bridge
-  **PowerPAK 1212-8SLW**  
3.3 x 3.3 mm<sup>2</sup>

## Benefit to Designs

- Low  $R_{DS(ON)}$  for improving efficiency in high current applications
- Top-cooled package options optimized for external heatsinks or housings
- Integrated solutions that reduce component counts and simplify designs

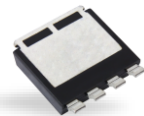


# High Power DC/DC and Synchronous Rectification



**TO-247AD**  
 Superjunction E-Series  
 650 V

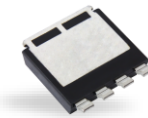
**MaxSiC 750 V – 1200 V**



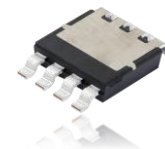
**PowerPAK 8x8L**  
 8 x 8 mm<sup>2</sup>  
 TrenchFET Gen IV & V  
 80 V – 150 V



**PowerPAK 8x8LR**  
 Top-cooled 8 x 8 mm<sup>2</sup>  
 TrenchFET Gen IV & V  
 80 V – 150 V



**PowerPAK 8x8L**  
 8 x 8 mm<sup>2</sup>  
 TrenchFET Gen IV  
 40 V – 80 V

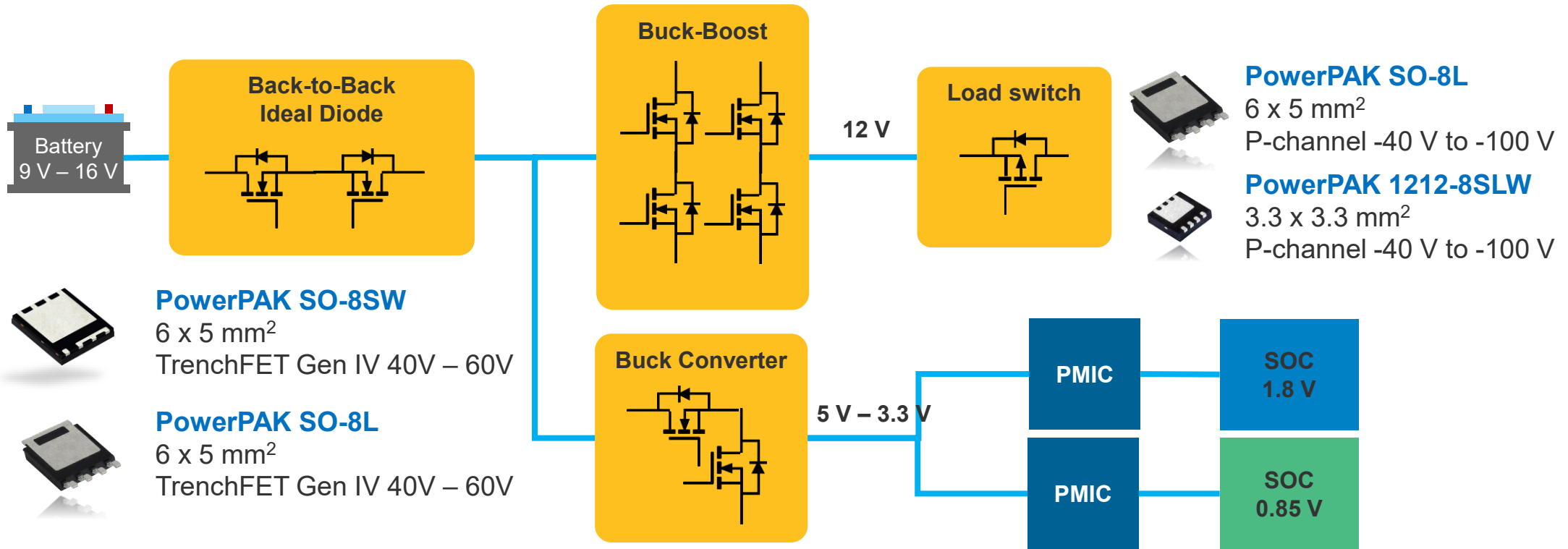


**PowerPAK 8x8LR**  
 Top-cooled 8 x 8 mm<sup>2</sup>  
 TrenchFET Gen IV  
 40 V – 80 V

## Benefit to Designs

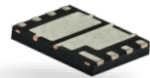
- Low  $R_{DS(ON)}$  and FOM for efficiency
- Top-cooled package optimized for external heatsinking
- Low  $R_{DS}^*$  footprint enabling high power density

# Buck Converters for 12 V Systems



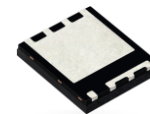
## Benefit to Designs

- High current solutions
- Low  $R_{DS(ON)}$  and FOM for efficiency
- Component reduction with integration
- Logic-level devices



### PowerPAIR 6x5FSW

6 x 5 mm<sup>2</sup>  
TrenchFET Gen IV 40 V



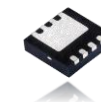
### PowerPAK SO-8SW

6 x 5 mm<sup>2</sup>  
TrenchFET Gen IV 40 V – 60 V



### PowerPAK SO-8L

6 x 5 mm<sup>2</sup>  
TrenchFET Gen IV 40 V – 60 V



### PowerPAK 1212-8SLW

3.3 x 3.3 mm<sup>2</sup>  
TrenchFET Gen IV 40 V – 60 V



# Emerging E-Motorcycle / E-Mobility Applications



## Fun Concept

Equivalent to mid-sized ICE motorcycles with fixed battery, offering combined charging system Type 2 (CCS2) connectors



## Urban Concept

Urban electric mobility, function-focused and using in-house developed (Honda and Panasonic) battery packs



## Swappable Battery

48 V / 1.3 KW In production, and compatible to e-scooters manufactured by Yamaha, Kawasaki, and Suzuki

Following the launch of the e-scooter lineup in 2019, Honda revealed two new e-motorcycle models, fun concept and urban concept, at EICMA 2024 to replace mid-sized ICE motorcycles in the future and to completely electrify the two-wheel products by the 2040s.

# Capacity Investment

Growth Support

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# Auto MOSFET Front-End Capacity Expansion by Location

- **12 in Germany fab under construction**
  - **New 12 in fab** in Itzehoe – volume ramp up of stage 1 in 2027
- **Foundry partnership**
  - Tower Semiconductor – already in production
  - Key foundries - KF ramp up in 2025
- **Vishay acquired Newport fab in UK**
  - 8 in FE production for silicon in 2025 (n-/p- channel)



Itzehoe, Germany 8 in fab expanding to 12 in fab



8 in Newport Fab, UK (Si & SiC)



# Automotive Backend Packaging Expansion Plans

- **Simconix – Shanghai (Internal BE)**

Die sort, assembly and test, focus on legacy and advanced packages

- **Kaohsiung Taiwan**

R&D, die sort, assembly and test for legacy and advanced packages

Expanding capacity and qualifying additional parts to avoid tariffs

- **Manila, Philippines**

Wafer plating, probing and final test

- **OSAT Partnership**

ATX Malaysia - DPAK & D<sup>2</sup>PAK transfers

- 80+ DPAK/D<sup>2</sup>PAK parts are being transferred to ATX with ramp-up starting H1'26

OSAT SOT23/PPAK1212W/PPAKSC-70W – planned customer samples by Q2'26

OSAT PPAKSO-8L, 8x8L, 1212-8SLW, SO-8SW – planned customer samples by Q3'26

OSAT PPAK SO-8L Dual/PPAK8x8LR/SO-10LR – planned customer samples by H1'27



# Design Resources and Tools

Growth Support

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# Design Resources

- **Product Page**
  - Datasheet
  - Package information
  - PAD pattern
  - Tape and reel
  - FIT / reliability information
  
- **Sell Sheet and Infographic**
  
- **PSpice Model**
  
- **PMOS Tech Support:** [pMOStechsupport@vishay.com](mailto:pMOStechsupport@vishay.com)

# Product Page



## SQJQ140E PRODUCT INFORMATION

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

### FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % RG and UIS tested

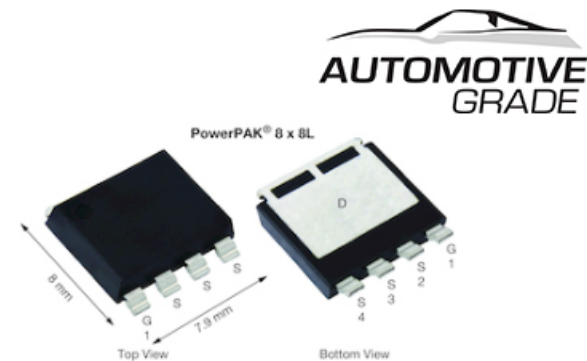
[Datasheet](#)

[Request Sample](#)

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### ECAD Models

[\(Download from Ultra Librarian\)](#)



Documents

Design Tools

Quality

Technical Questions

Showing 1 to 11 of 11 entries

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Document Type	Title	Description	Share
Datasheet	<a href="#">SQJQ140E</a>	Automotive N-Channel 40 V (D-S) 175 °C MOSFET	
Ordering Info	<a href="#">SQ MOSFET Ordering Information</a>	Ordering Code for SQ Series Automotive MOSFET	
Packaging Information	<a href="#">Reel Information</a>	Reel	
Packaging Information	<a href="#">PAD Pattern</a>	Recommended Land Pattern PowerPAK® 8 x 8L BWL	
Packaging Information	<a href="#">Device Orientation</a>	Device Orientation for PowerPAK 8 X 8	
Packaging Information	<a href="#">Tape Information</a>	PowerPAK® 8 x 8L CARRIER TAPE	
Package Drawings	<a href="#">Package Information</a>	PowerPAK® 8 x 8L Case Outline 2	
Reliability Data	<a href="#">Product Reliability</a>	530MC SG Process Technology	
Reliability Data	<a href="#">Product Reliability</a>	Environmental and Package Testing Data for PowerPAK 8 x 8L BWL Automotive	
Sell Sheet	<a href="#">Sell Sheet</a>	SQJQ140E MOSFET - CN	
Sell Sheet	<a href="#">Sell Sheet</a>	SQJQ140E MOSFET	



## [Link: Document Library | Vishay](#)

### Select Sell Sheet **Select MOSFET**

Product Category

Document Type

- Sell Sheet

Reset

Semiconductors

- Die and Wafer
- Diodes and Rectifiers
- Discrete Thyristors
- ICs - Power and Linear
- MOSFETs
- Optoelectronics
- Power Modules

Reset

Passive Components

- Capacitors
- Magnetics
- Other Components
- Resistors
- Sensors

Reset

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Title ▲▼	Product Category ▲▼	Document Type ▲▼	Date ▲▼	Share
SQJ182ER Top-Cooled Automotive MOSFET	MOSFETs, Automotive	Sell Sheet	September 11, 2025	<a href="#">✉</a>
SQJ590EP Best in Class Automotive MOSFET	MOSFETs, Automotive	Sell Sheet	September 5, 2025	<a href="#">✉</a>
SQJ211ELP Best in Class Automotive MOSFET (CN)	MOSFETs, Automotive	Sell Sheet	September 2, 2025	<a href="#">✉</a>
SQJ211ELP Best in Class Automotive MOSFET	MOSFETs, Automotive	Sell Sheet	September 2, 2025	<a href="#">✉</a>
SQZF140ELPW Integrated 40 V Half-Bridge MOSFETs (JP)	MOSFETs, Automotive	Sell Sheet	June 11, 2025	<a href="#">✉</a>
SQJQ184ER Top-Side Cooled Automotive N-Channel 80 V MOSFET (CN)	MOSFETs, Automotive	Sell Sheet	April 8, 2025	<a href="#">✉</a>
SQZF140ELPW Integrated 40 V Half-Bridge MOSFETs	MOSFETs, Automotive	Sell Sheet	April 2, 2025	<a href="#">✉</a>
SQJQ140ER Top-Side Cooled Automotive 40 V MOSFET (JP)	MOSFETs, Automotive	Sell Sheet	March 31, 2025	<a href="#">✉</a>
SQJQ140E MOSFET - CN	MOSFETs, Automotive	Sell Sheet	June 4, 2024	<a href="#">✉</a>
SQJQ140E MOSFET	MOSFETs, Automotive	Sell Sheet	May 22, 2024	<a href="#">✉</a>
SiZF640DT Symmetric Dual N-Channel 40 V MOSFET	MOSFETs	Sell Sheet	May 22, 2024	<a href="#">✉</a>
SQJQ140ER Top-Side Cooled Automotive 40 V MOSFET	MOSFETs, Automotive	Sell Sheet	May 22, 2024	<a href="#">✉</a>
SQJQ184ER Top-Side Cooled Automotive N-Channel 80 V MOSFET	MOSFETs, Automotive	Sell Sheet	May 22, 2024	<a href="#">✉</a>

# Sell Sheet Example – SQZF140ELPW



**VISHAY**  
The DNA of tech.™

**SQZF140ELPW Integrated 40 V Half-Bridge MOSFETs**  
**Enabling More Compact and Efficient Automotive Power Management Systems**

**SQZF140ELPW Integrated 40 V Half-Bridge MOSFET**

**ADVANTAGE**

The SQZF140ELPW reduces component counts and enables higher switching frequencies and power density for DC/DC converter designs.

**MARKETS AND APPLICATIONS**

- MOBILITY**
- Automotive
  - 12 V systems
  - Battery management
  - DC/DC converters, including synchronous buck
  - Motor drive control

- KEY PRODUCT FEATURES**
- AEC-Q101 qualified,  $T_j = +175\text{ }^\circ\text{C}$
  - Two internally connected MOSFETs in a half-bridge configuration
  - Internally formed switch node reduces external PCB traces and associated parasitics
  - Optimized pin configuration for synchronous buck and buck-boost converters
  - Wettable flanks promote solder fillet formation and enables AOI

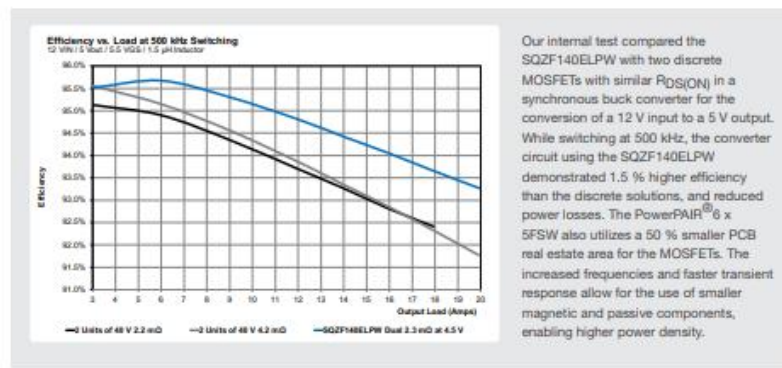
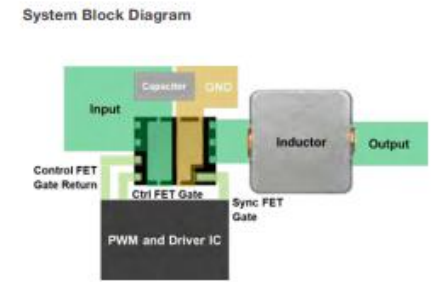
2 discrete packages ~62 mm<sup>2</sup>

**PowerPAIR integrated solution ~31 mm<sup>2</sup>**

**Key Product Benefits**

On-resistance	↓
$R_{DS(on)}$ FOM	↓
Power losses	↓
Component count	↓
PCB real estate requirement for MOSFETs	↓
Passive and magnetic component size	↓
Energy efficiency	↑
Current output	↑
Power density	↑
Board-level reliability	↑

- ADDITIONAL BENEFITS**
- Integration reduces component count - combining high side "control" FET and low side "synchronous" FET in a single package
  - Achieves higher efficiency at higher switching frequencies than discrete components, allows use of smaller capacitors and magnetic components
  - Simplifies PCB designs
  - Low  $R_{DS(on)}$  reduces power loss
  - Logic level operation



**RESOURCES**

Product Page Related Documents Contact Us

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# Infographics



Link: [Infographics, MOSFETs | Vishay](#)

## AUTOMOTIVE TrenchFET®

SQ SERIES POWER MOSFETS

- Wide range of n- and p-channel MOSFETs
  - N-ch  $V_{DS} = 12\text{ V to } 300\text{ V}$
  - P-ch  $V_{DS} = -12\text{ V to } -200\text{ V}$
- Available in single, dual, and dual asymmetric configurations
- Highly efficient packages with power density up to  $11\text{ W/mm}^2$ 
  - $R_{DS(on)}$  down to  $0.9\text{ m}\Omega$
- AEC-Q101 qualified to  $+175\text{ }^\circ\text{C}$
- Latest trench technologies optimized for low conduction and low switching losses
- Product testing includes extended temp screening with dynamic PAT, SYL, and SBL to reduce defects

N- and P-Channel MOSFETs

AEC-Q101 Qualified

### APPLICATIONS

AUTOMOTIVE

CAR BATTERIES

INFOTAINMENT

LIGHTING

BRAKING

ELECTRIC VEHICLES

POWER TRAIN

### Compact PowerPAK® packages ~ optimized for high board-level reliability

PowerPAK® 8x8L 8 mm x 8 mm	PowerPAK® SO-8L 5 mm x 6 mm	PowerPAK® 1212 3.3 mm x 3.3 mm	PowerPAK® SC-70 2 mm x 2mm	KGD Known Good Die 1 m x 1 mm to 8 mm x 12 mm

### SQ Package Portfolio

Package	Voltage Range (V)
SC-70	~40
SO-8	~100
SO-8L	~100
1212	~100
SC-70	~100
8x8L	~100
TO-247	~100
TO-220	~100
TO-18	~100

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MS7533-2007

## SQJ180EP 80 V Automotive MOSFET

3.3 mΩ in PowerPAK® SO-8L With Secure-Mounting Gull-Wing Leads

Reliability + Efficiency + Power Density

**SQJ180EP**

AUTOMOTIVE GRADE

### BETTER SWITCHING EFFICIENCY FOR AUTOMOTIVE

- Optimized  $R_{DS}$  x  $Q_g$  FOM reduces loss from gate driving and increases efficiency
- 21 % improvement over prior generation SQA78EP
- 43 % better than the next best product with gull-wing leads

### 54 % LOWER $R_{DS(on)}$ THAN THE NEXT BEST 80 V, N-CHANNEL DEVICE IN SIMILAR FOOTPRINT WITH SECURE-MOUNTING GULL-WING LEADS

Device	Maximum $R_{DS(on)}$ (mΩ) at 10 V
Competitor LPAK	7.8
Prior Generation	5.3
<b>SQJ180EP</b>	<b>3.3</b>

### BETTER BOARD-LEVEL RELIABILITY AND MORE POWER DENSITY

- Gull-wing leads improve resilience for mechanical stress and TCE mismatch
- Rugged, reliable, and reduces up to 80 % PCB real estate for MOSFET from D<sup>2</sup>PAK
- Passed all these BLR tests:

BENDING TEST

VIBRATION TEST

RAPID THERMAL CYCLE TEST

POWERED TEMP CYCLE TEST

### TYPICAL $R_{DS} \times Q_g$ FOM (mΩ x nC) at 10 V

Device	Typical $R_{DS} \times Q_g$ FOM (mΩ x nC)
Competitor LPAK	373
Prior Generation	268
<b>SQJ180EP</b>	<b>211</b>

### FOR 48 V, 24 V, AND 12 V AUTOMOTIVE APPLICATIONS

TRANSMISSION CONTROL

POWERTRAIN

DC/DC CONVERTERS

SOLENOID DRIVE

MOTOR DRIVE

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pmosetechsupport@vishay.com

IG1794891-2008

# Automotive / AEC-Q101 MOSFETs for Aerospace and Defense Applications



- > 200 auto MOSFET part numbers selected to support aerospace and defense customer programs
- Package types supported in Taiwan
  - SOT-23, TSOP6, PPAK 1212-8W, PPAK SO-8L (single / dual), PPAK 8x8L, SO-8, DPAK/D<sup>2</sup>PAK
- Selector guide / brochure available to review with MarCom
- Customers targeted for initial visits
  - US – Lockheed, L3Harris, Honeywell, DRS
  - EU – Leonardo, Thales (Pure consortium)
  - Israel – Rafael, IAI Elta, Kratos, Elbit



POWER MOSFETS FOR AVIONICS, MILITARY, AND  
Automotive-Grade Low and Medium Voltage Gate-Trench Silicon Solutions



POWER MOSFETS FOR AVIONICS, MILITARY, AND  
Automotive-Grade Low and Medium Voltage Gate-Trench Silicon Solutions

VISHAY INTERTECHNOLOGY,

**Power MOSFET Solutions for Avionic, Military, and Space**  
Product Selector Guide

**Product Features**

- Wide voltage range offering P-Ch (-150V to -12V) and N-Ch (20V-300V)
- Gen IV and Gen V gate-trench process
- Low  $R_{DS(on)}$  devices for higher efficiency and increased power density
- Advanced packages for higher thermal efficiency

**Package Options**

- PowerPAK SO-8L Single & Dual
- PowerPAK 8x8L
- PowerPAK 1212-8W Single & Dual
- DPAK (TO-252) & D<sup>2</sup>PAK (TO-263)
- SOT-23, TSOP6 (Single & Dual), SO-8 (Single & Dual)

**Package Options**

Vishay's automotive-grade power MOSFETs combine advanced silicon and package technologies supporting the increased demand for reliability, efficiency, and power density. With unmatched reliability and rugged process and package design, Vishay's power MOSFETs are the trusted choice for avionics, defense and space systems requiring high performance in extreme environments. Engineered for excellence, our advanced low to medium voltage gate-trench silicon processes deliver superior performance, durability and reliability for cutting-edge aerospace and defense systems.

**Resources**

- For technical support, contact [pmstechsupport@vishay.com](mailto:pmstechsupport@vishay.com)
- For further information, visit [www.vishay.com/en/mosfets/automotive-mosfets/](http://www.vishay.com/en/mosfets/automotive-mosfets/)
- Engineer's Toolbox:




inverters and DCDC

ration.  
eling for higher power

higher switching

and signal/power



ng, Pressure Pot,

Cycling (2600 cycles)



-outline packages.

$Q_{th} [mC]$	$V_{DS(on)} [V]$	$R_{\theta(jc)} [C]$
13	1.4	1.1
24	1.5	0.43
19	1.5	0.41
25	1.5	0.49
19	1.5	1
14	1.3	1.37
9	1.3	4.11
10	1.5	0.72
11.8	1.5	2.7
5.5	2.2	1.5
5	2.5	2.2
7	2.5	2.2
11	1.2	1.5
6	1.5	2.67
8	2.5	0.5
18	2.5	1.5
6	2.5	4
2	2.2	0.9
4	1.5	1.8
12.5	1.5	1.9
3	2.2	1.2
7	1.5	1.4
5	2.5	1.5
5	2.5	1.06
8	1.5	0.44
16	2	0.9
15	2.5	0.8
13	2.5	1
6	2.5	1.4
6	2	1.2
6	2	2
5.5	2.5	1.6
3	1.2	1.9
3.2	1.2	1.48
5	1.2	1.4
15	1.2	1.55
9	1.2	2.54
6	2.5	2.54
4	2.5	1.84
7	1.5	0.52
4.5	1.5	4

3/8

# Pspice

- Our PSpice models are compatible with
  - Synopsis HSpice
  - Cadence / Orcad PSpice
  - Analog Devices / LTSpice
- SPICE models are derived from the physical characteristics of MOSFETs as measured and guaranteed in the datasheet. Models are verified to represent device properties at release and to be free of syntax errors
- Models are available upon request - [pMOStechsupport@vishay.com](mailto:pMOStechsupport@vishay.com)



# Nomenclature for Surface-Mount Packages



**SQ**

Product Grade

**SQ: Automotive**  
**Si: Commercial**

**J**

PPAK SO8L

Package

**JK**

PPAK 10x15

**JQ**

PPAK 8x8L

**RQ**

PPAK 8x8SW

**RS**

PPAK SO-8SW

**ZF or ZF3**

ZF – PPAIR 6x5FSW  
ZF3 – PPAIR 3x3FSW

**4 or 9**

SO-8  
4 – Single  
9 – Dual

**S or 7**

PPAK 1212-8W  
PPAK 1212-8SLW

**34 / 35**

TSSOP6

**23**

SOT23

**1 or A**

PPAK SC70

**X**

$V_{DS}$

**X: Al wire**  
**A: Al wire**  
**1: Clip / BWL**  
**5: Gen V**  
**6: Gen VI**

**XX**

Polarity

**N-channel: even**  
**3-4-5x: 40 v**  
**6x: 60 v**  
**8x: 80 v**  
**1x: 100 V**  
**9x: 150 V & 200 V**  
**P-channel: odd**  
**4x: -40 v**  
**6x: -60 v**  
**8x: -80 v**

**XXXX**

Features

**A, B, C, F: revisions or cost reduced**

**E:  $T_J$  max = 175 °C**

**EJW: 2x2 + wettable flanks**

**ENW: 3x3 + wettable flanks**

**EPW: 6x5 + wettable flanks**

**EP:  $T_J$  max = 175 °C**

**ER: reversed leads & 175 °C**

**EL: logic level**

**ELNW: logic level + wettable flanks**

**ELPW: logic level + wettable flanks**

**ELR: logic level + reverse leads**



**AEQ-101 qualified part numbers begin with SQ prefix**

# Nomenclature for Transistor-Outline Packages

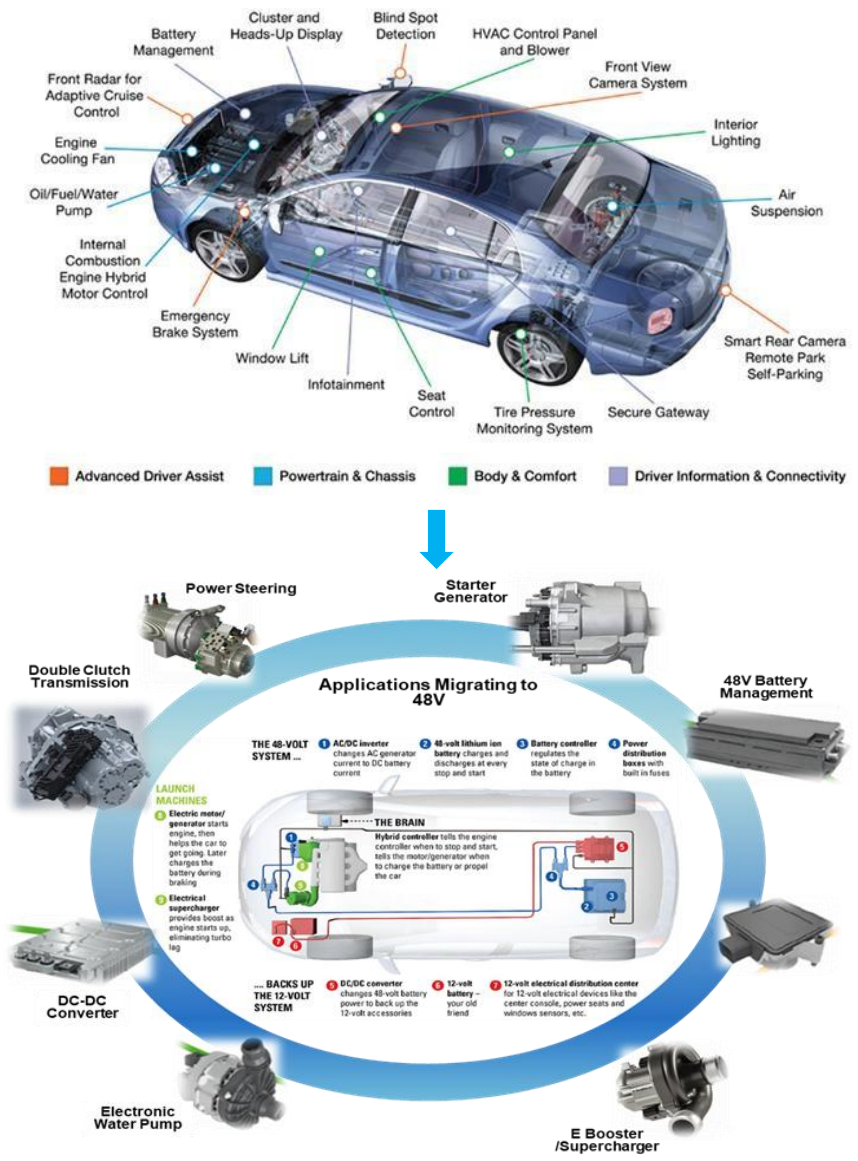


<b>SQ</b> Product Grade	<b>M</b> <sup>D2PAK</sup> Package	<b>X</b> $V_{DS}$	<b>XXX</b> $R_{DS(ON)}$	<b>X</b> Polarity	<b>XX</b> Features
SU: Commercial SQ: Automotive	<b>D</b> DPAK	2: $\leq 25$ V 3: 30 V 4: 40 V	001 (1 m $\Omega$ )	N P 0 1 2 3	E: $T_J$ max = 175 °C L: logic level M: D <sup>2</sup> PAK-7L, 175 °C
	<b>P</b> TO-220	5: 60 V 6: 80 V	010 (10 m $\Omega$ )	4 5 6 7	EL: 175 °C & logic level
	<b>U</b> IPAK	7: 100 V 8: 150 V 9: 200 V	100 (100 m $\Omega$ )	8 9	
	<b>W</b> TO-247AC	1: $\geq 250$ V			

New nomenclature applies to new TO devices featuring ThunderFET<sup>®</sup> and TrenchFET<sup>®</sup> Gen IV

# Summary of 2026 Strategic Objectives

- **Focus on print position at selected growth customers**
  - New product releases and roadmaps are well aligned to the key electrification applications and also support traditional ICE engine management systems
- **Aggressively close the loop on PCNs / PTNs**
  - Transfers to Newport and Key foundries
  - Cost reductions to copper wire “C” suffix
- **Identify customers and define marketing actions to grow POS share**
- **Relaunch MaxSiC product family with refreshed roadmap**
  - First 1200 V Gen 2 products available
  - Initial releases aligned to power supplies / renewables
  - Top-side cooled packages for automotive in development
- **Identify and follow up with aerospace and defense customers where AEC-Q101 qualification is a competitive advantage**
- **Close outstanding quality / application issues with key customers, including Denso and Valeo**





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Thank You  
Think Customer First

